

Wavelength range	Type	Technology	Electrodes
Red-Infrared, selective	Integrated filter	AlGaAs/GaAs	P (anode) up

	typ. dimensions (µm)	
	<u>typ. thickness</u> 260 (±20) µm <u>anode</u> gold alloy, 1.5 µm <u>cathode</u> gold alloy, 0.5 µm	Description Red-infrared-selective photodiode with special response range (650-820 nm) Applications Optical communications, safety equipment, light barriers

Miscellaneous Parameters

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Active area		A	5,8	mm ²
Operating temperature range		T _{amb}	-40 to +125	°C
Storage temperature range		T _{stg}	-40 to +125	°C

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Dark current	V _R = 1 V	I _D		2	10	nA
Responsivity at λ _P ¹	V _R = 0 V	S _λ		0.4		A/W
Peak sensitivity	V _R = 0 V	λ _P		740		nm
Spectral range at 50 %	V _R = 0 V	λ _{0.5}	650		820	nm
Spectral bandwidth at 50%	V _R = 0 V	Δλ _{0.5}		170		nm
Junction capacitance	V _R = 0 V	C _J				pF
Switching time	V _R = 1 V	t _r , t _f				ns

¹Measured on bare chip on TO-header

Labeling

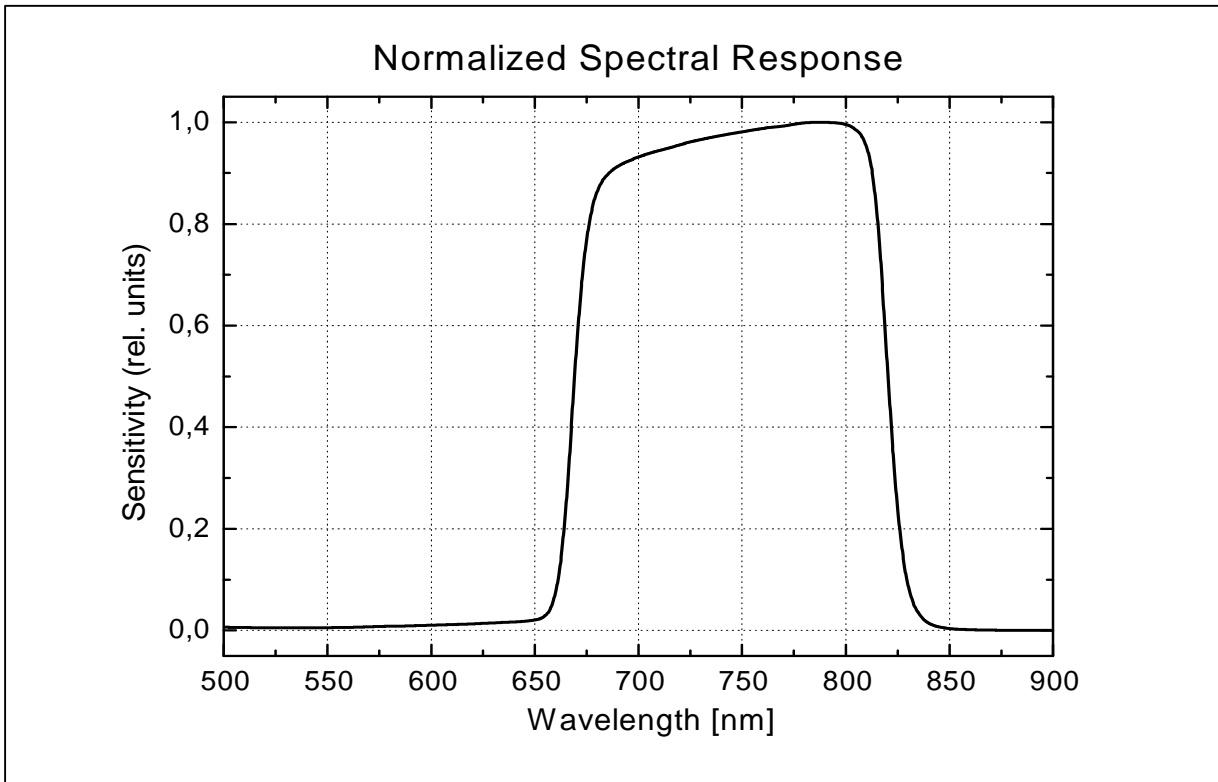
Type	Typ. I _D [pA]	Typ. S _λ [A/W]	Lot N°	Quantity
EPC-740-2.5				

Packing: Chips on adhesive film with wire-bond side on top

*Note: All measurements carried out with *EPIGAP* equipment

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.

preliminary spectrum



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